TOSHIBA Field Effect Transistor Silicon N Channel MOS Type  $(\pi - MOSVII)$ 

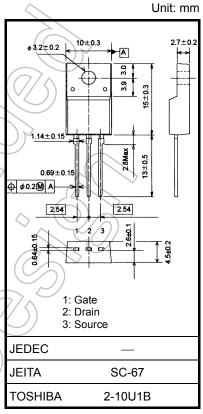
# TK4A60DA

## **Switching Regulator Applications**

- Low drain-source ON resistance: RDS (ON) =  $1.7 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 2.2 \text{ S (typ.)}$
- Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 600 \text{ V)}$
- Enhancement-mode:  $V_{th} = 2.4 \text{ to } 4.4 \text{ V (VDS} = 10 \text{ V, ID} = 1 \text{ mA)}$

### Absolute Maximum Ratings (Ta = 25°C)

| Characteristics                        |                | Symbol               | Rating     | Unit             |  |  |
|--|----------------|----------------------|------------|------------------|--|--|
| Drain-source voltage                   |                | $V_{DSS}$            | 600        | $(\checkmark v)$ |  |  |
| Gate-source voltage                    |                | $V_{GSS}$            | ±30        | A                |  |  |
| Drain current                          | DC (Note 1)    | I <sub>D</sub>       | 3.5        | A                |  |  |
|  | Pulse (Note 1) | I <sub>DP</sub>      | 14         | > ^              |  |  |
| Drain power dissipation                | on (Tc = 25°C) | $P_{D}$              | 35         | W                |  |  |
| Single pulse avalanche energy (Note 2) |                | EAS                  | 158        | mJ               |  |  |
| Avalanche current                      |                | I <sub>AR</sub>      | 3.5        | A                |  |  |
| Repetitive avalanche energy (Note 3)   |                | EAR                  | 3.5        | mJ               |  |  |
| Channel temperature                    |                | Tch                  | 150        | √ °C             |  |  |
| Storage temperature range              |                | (T <sub>stg</sub> )) | -55 to 150 | //°C             |  |  |



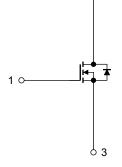
Weight: 1.7 g (typ.)

Note: Using continuously under neavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

| Characteristics                        | Symbol                 | Max  | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case    | Rth (ch-c)             | 3.57 | °C/W |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 62.5 | °C/W |

Internal Connection



Note 1: Please use devices on conditions that the channel temperature is below 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 22.5 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 3.5 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

Start of commercial production 2008-09

## Electrical Characteristics (Ta = 25°C)

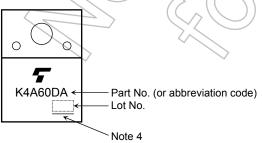
| Char                               | acteristics    | Symbol               | Test Condition   | Min        | Тур.  | Max                 | Unit |
|------------------------------------|----------------|----------------------|--|------------|-------|---------------------|------|
| Gate leakage cu                    | rrent          | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$                          | _          | _     | ±1                  | μΑ   |
| Drain cut-off curr                 | ent            | I <sub>DSS</sub>     | V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V                             | _          | _     | 10                  | μА   |
| Drain-source bre                   | akdown voltage | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V                              | 600        | _     | _                   | V    |
| Gate threshold v                   | oltage         | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA                              | 2.4        | _     | 4.4                 | V    |
| Drain-source ON                    | resistance     | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.8 A                             | 1          | ) 1.7 | 2.2                 | Ω    |
| Forward transfer                   | admittance     | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.8 A                             | 0.6        | 2.2   | _                   | S    |
| Input capacitance                  |                | C <sub>iss</sub>     |  | ()         | 490   | _                   |      |
| Reverse transfer capacitance       |                | C <sub>rss</sub>     | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$           | _          | 3     | _                   | pF   |
| Output capacitance                 |                | C <sub>oss</sub>     |  | 7 —        | 55    | _                   |      |
| Switching time                     | Rise time      | t <sub>r</sub>       | 10 V<br>VGS ID = 1.8 A VOUT  | _          | 18    | <i>&gt;&gt;&gt;</i> |      |
|                                    | Turn-on time   | t <sub>on</sub>      | 0 V — \$ R <sub>L</sub> = 111 Ω  | -(         | 40    | > —                 | ns   |
|                                    | Fall time      | t <sub>f</sub>       | V <sub>DD</sub> ≈ 200 V  |            | (8)   | ) _                 | 110  |
|                                    | Turn-off time  | t <sub>off</sub>     | Duty ≤ 1%, t <sub>W</sub> = 10 μs  | (A)        | 55    | _                   |      |
| Total gate charge Qg               |                |                      | $\sim$   | 11         |       |                     |      |
| Gate-source charge Q <sub>gs</sub> |                | Qgs                  | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3.5 \text{ A}$ | <i>)</i> — | 6     |                     | nC   |
| Gate-drain charge Q <sub>gd</sub>  |                |                      |  | 5          |       |                     |      |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol             | Test Condition                                  | Min | Тур. | Max  | Unit |
|---|--------------------|---|-----|------|------|------|
| Continuous drain reverse current (Note 1) | )) I <sub>DR</sub> | (7/s) <u>-</u>                                  | _   | _    | 3.5  | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub>   |   | _   | _    | 14   | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub>   | $I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V}$  | _   | _    | -1.7 | V    |
| Reverse recovery time                     | trr                | $I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V},$ | _   | 1000 | _    | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>    | dl <sub>DR</sub> /dt = 100 A/μs                 | _   | 5.0  | _    | μС   |

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# Marking

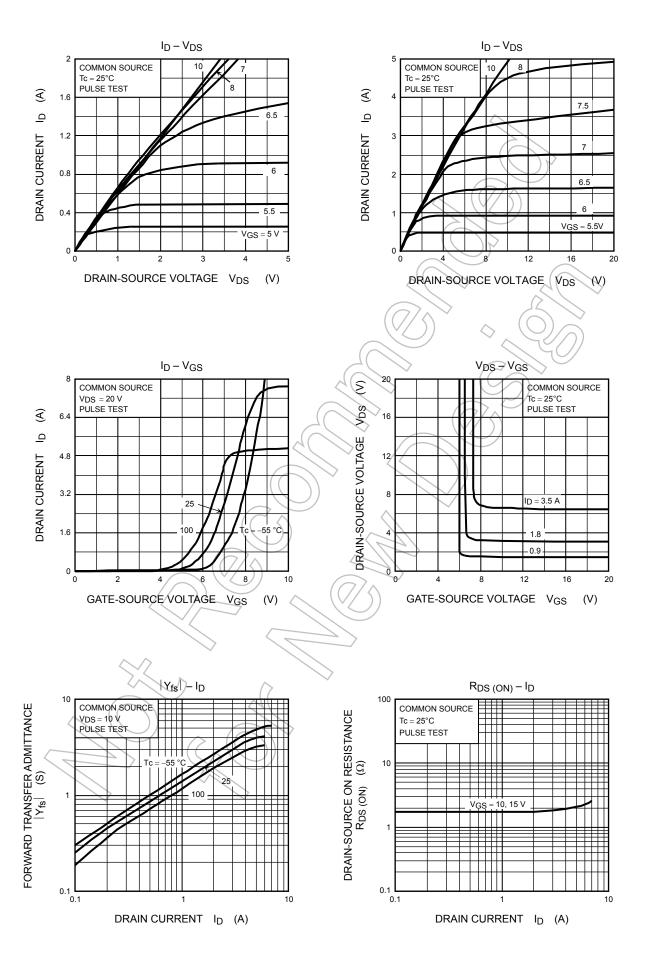


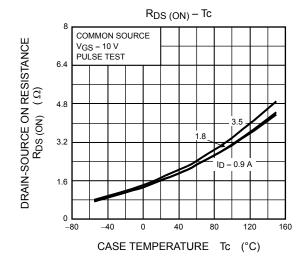
Note 4: A line under a Lot No. identifies the indication of product Labels.

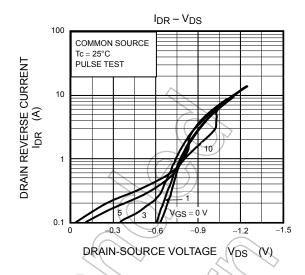
Not underlined: [[Pb]]/INCLUDES > MCV

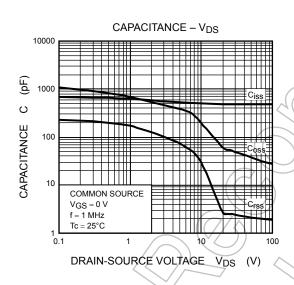
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

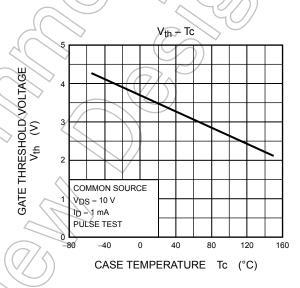
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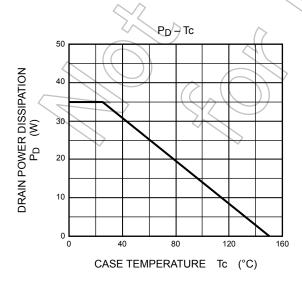


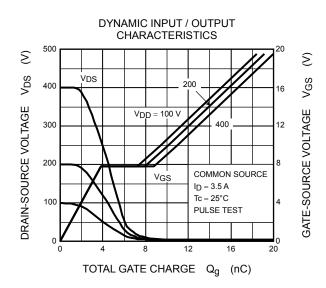


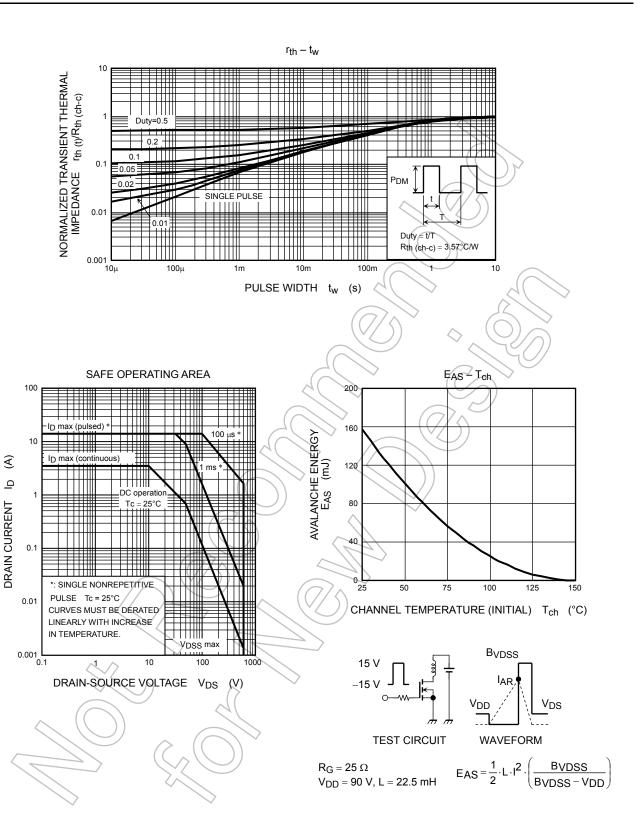












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